

# LITHOGRAPHY SERVICES

## DUV Photoresist: 193nm Spin Coating TOK P6111

### Features

- 100% Defect Free Coating
- <1% Within Wafer Non-Uniformity

### Blanket Coating

Incoming Inspection of Wafer, 100%
Photoresist Application
Softbake: T=3 Minutes, T <sub>A</sub> =125°C
Cool
Final Inspection, 100%

### Equipment

Coater	Brewer Scientific
Hot Plate – Bake	
Chill Plate – Cool	

### Chemical

Photo Resist	TOK P6111
EBR Solvent	Microchem (Shipley Product) EC11

### Standard Specifications

Thickness Range	1,600A – 2,000A	
Non-Uniformity	Intra-Wafer	<1%, up to 5mm EBR
Wafer-to Wafer Uniformity	±2%	
EBR	Edge Bead Removal	1mm
100% Contamination Free		

### Quality Guarantee

100% Defect Free Coating, no backside contamination.

### Required Specifications

Thickness	1,600A – 2,000A
EBR	0 – 5mm

### Wafer Size

mm	Inches
100	4
125	5
150	6
200	8
300	12

Note: Blanket spin quality and intra-wafer uniformity are dependant upon wafer quality, surface scratches, embedded particles, and etch imperfections. Embedded particles will cause "comet tails", striations and various other coating anomalies. Even faint surface scratches will be visible after resist coating, as resist coatings do not cover wafer imperfections; surface particles and scratches are highlighted and decorated.